

other. The result is an effective channel length, L , which is independent of the original disposable gate length. Fabrication then proceeds in standard manner to complete the device.”

Amend paragraph [0017] to read as follows:

[0017] As a second embodiment, the low V_T channel implant can be performed prior to the high V_T implant. After removal of the disposable gate, disposable sidewalls are formed on the mask as in FIGURE 1B of the first embodiment and as shown in FIGURE 2A wherein like reference characters refer to the same or similar structure. The sidewall on the source region side 11 is retained and the sidewall on the drain region side 13 is removed with appropriate deposition and patterning of resist and etching in standard manner. A low V_T region 21 [implant] is then provided by implant [into the exposed portion 21] of the channel as shown in FIGURE 2B. The remaining sidewall 11 at the source end of the channel is then removed and a high V_T implant is implanted into the channel region between the source and drain regions. Preferably, the high V_T implant is of opposite conductivity type to the low V_T implant to provide a high V_T region 23 and a low V_T region 21. Fabrication then proceeds in standard manner to complete the device. Optionally, the high V_T implant can be performed prior to formation of the sidewalls.”

Amend paragraph [0018] to read as follows:

“[0018] As a third embodiment, it is desirable to add a liner 25 over the mask surface, sidewalls and pad oxide prior to fabrication as noted above with reference to the first and/or second embodiments and particularly over the structure as shown in FIGURE 1A and the structure as shown in FIGURE 2A prior to formation of the sidewalls 11, 13 with subsequent formation of the sidewalls 11, 13 over the liner as shown in FIGURE 3B. The liner 25 is